

**PATENT APPLICATION****Docket No. 2522-040****Client No. AW8072US/MJ**

Applicant: Jae-Jong HAN, Yong-Woo HYUNG, Seung-Mok SHIN, Kong-Soo LEE and Eun-Jung YUN

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Title: METHOD OF FORMING A GATE ELECTRODE, METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE HAVING THE GATE ELECTRODE, AND METHOD OF OXIDIZING A SUBSTRATE

**INFORMATION DISCLOSURE CITATION  
FORM PTO-1449 (Modified)****U.S. PATENT DOCUMENTS**

<u>Exam Init</u>	<u>Ref</u>	<u>Document Number</u>	<u>Issue Date</u>	<u>Name</u>	<u>Class</u>	<u>Sub Class</u>
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**FOREIGN PATENT DOCUMENTS**

<u>Exam Init</u>	<u>Ref</u>	<u>Document Number</u>	<u>Publication Date</u>	<u>Country</u>	<u>Name</u>
_____	_____	JP8032066	2/2/1996	Japan	Katsuichi
_____	_____	JP11345970	12/14/1999	Japan	Tomio et al.

**OTHER DOCUMENTS**

<u>Exam Init</u>	<u>Ref</u>	<u>Author, Title, Date, Pertinent Pages, Etc.)</u>
_____	_____	English language of Abstract for Japanese Patent Publication No. JP8032066, filed 2/2/1996.
_____	_____	English language of Abstract for Japanese Patent Publication No. JP11345970, filed 12/14/1999.

Examiner: \_\_\_\_\_

Date Considered: \_\_\_\_\_